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deposition (LPCVD), rapid thermal chemical vapor deposition (RTCVD) or atomic layer deposition (ALD).

**11.** A method according to claim **10**, wherein the silicon nitride film has a thickness of approximately 50 to 200 Å.

**12.** A method according to claim **7**, wherein the second hardmask layer comprises a poly-silicon or an amorphous silicon film.

**12**

**13.** A method according to claim **12**, wherein the silicon film is deposited via low pressure chemical vapor deposition (LPCVD), rapid thermal chemical vapor deposition (RTCVD) or atomic layer deposition (ALD).

**14.** A method according to claim **12**, wherein the silicon film has a thickness of approximately 100 Å to 300 Å.

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